NSN 5962-01-420-7510

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View Online at https://aerobasegroup.com/nsn/5962-01-420-7510

Bodv	

Between 0.442 inches and 0.460 inches

Body Width:

Between 0.442 inches and 0.460 inches

Body Height:

Between 0.060 inches and 0.100 inches

Maximum Power Dissipation Rating:

1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Pacer dawn

Features Provided:

Asynchronous and burn in, mil-std-883, class b and electrostatic sensitive and monolithic and programmed and tested to mil-std-883

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Criticality Code Justification:

Cbbl

Case Outline Source And Designator:

C-4 mil-m-38510

Current Rating Per Characteristic:

16.00 milliamperes reverse current, dc

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed (pal c22v10-25

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source and -2.0 volts input and 7.0 volts input

Capitance Rating Per Characteristic:

10.00 input picofarads and 10.00 output picofarads

Time Rating Per Chacteristic:

25.00 nanoseconds af output megawatts

Memory Device Type:

Pal

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Special Features:

Altered item programmed using 67268 5962-88670013a (which is 81349 m38510/50802b3a) using programming instruction 7816354p774

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 leadless

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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